2 1	Document ID Issue Da US 6222226 B1 20010424 US 6143606 A 20001107	D Issue Date Pages 1 20010424 13 20001107 9	Pages 13	Title Semiconductor memory device and method for manufacturing the same Method for manufacturing split-ga	and e same lit-gate	Current OR Current XRef
	US 6143606 A	20001107	9	Method for manufacturing split-gate flash memory cell	ing split-gate	438/257
ω	US 5631179 A 19970520	19970520	. 6	Method of manufacturing metallic source line, self-aligned contact for	g metallic ned contact	etallic contact 43
4	US 5459091 A 19951017	19951017	11	Method for fabricating a non-volatile memory device	Vice	ra 257/316 vice 438/257 ; 438/2

Double Sidewall Spacors